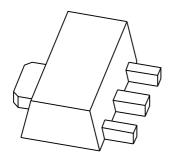
# **DISCRETE SEMICONDUCTORS**

# DATA SHEET



# BF620; BF622 NPN high-voltage transistors

Product data sheet Supersedes data of 1999 Apr 21 2004 Dec 14



# NPN high-voltage transistors

BF620; BF622

#### **FEATURES**

- Low current (max. 50 mA)
- High voltage (max. 300 V).

### **APPLICATIONS**

· Video output stages.

#### **DESCRIPTION**

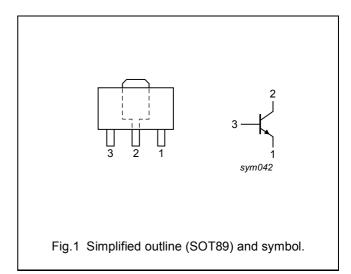
NPN high-voltage transistor in a SOT89 plastic package. PNP complements: BF621 and BF623.

### **MARKING**

TYPE NUMBER	MARKING CODE
BF620	DC
BF622	DA

#### **PINNING**

PIN	DESCRIPTION
1	emitter
2	collector
3	base



### **ORDERING INFORMATION**

TYPE NUMBER		PACKAGE	
TIPE NUMBER	NAME	DESCRIPTION	VERSION
BF620	SC-62	SC-62 plastic surface mounted package; collector pad for good heat SC	
BF622		transfer; 3 leads	

# NPN high-voltage transistors

BF620; BF622

#### LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

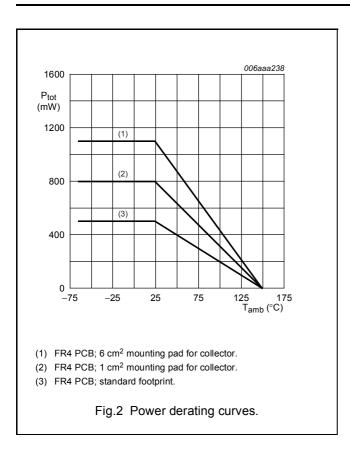
SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>CBO</sub>	collector-base voltage	open emitter			
	BF620		_	300	V
	BF622		_	250	V
$V_{CEO}$	collector-emitter voltage	open base			
	BF620		_	300	V
	BF622		_	250	V
$V_{EBO}$	emitter-base voltage	open collector	_	5	V
I <sub>C</sub>	collector current (DC)		_	50	mA
I <sub>CM</sub>	peak collector current		_	100	mA
I <sub>BM</sub>	peak base current		_	50	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C			
		note 1	_	0.5	W
		note 2	_	0.8	W
		note 3	_	1.1	W
T <sub>stg</sub>	storage temperature		-65	+150	°C
T <sub>j</sub>	junction temperature		_	150	°C
T <sub>amb</sub>	ambient temperature		-65	+150	∘C

### **Notes**

- 1. Device mounted on a printed-circuit board, single-sided copper, tin-plated and standard footprint.
- 2. Device mounted on a printed-circuit board, single-sided copper, tin-plated and mounting pad for collector 1 cm<sup>2</sup>.
- 3. Device mounted on a printed-circuit board, single-sided copper, tin-plated and mounting pad for collector 6 cm<sup>2</sup>.

# NPN high-voltage transistors

BF620; BF622



## NPN high-voltage transistors

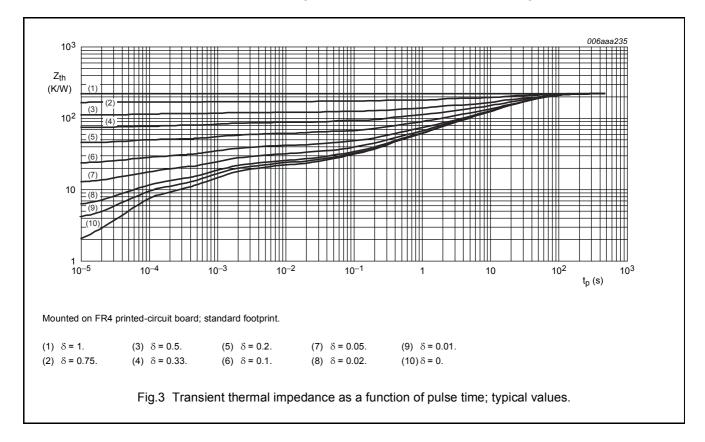
BF620; BF622

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th(j-a)</sub>	thermal resistance from junction to	in free air		
	ambient	note 1	250	K/W
		note 2	156	K/W
		note 3	113	K/W
R <sub>th(j-s)</sub>	thermal resistance from junction to soldering point		30	K/W

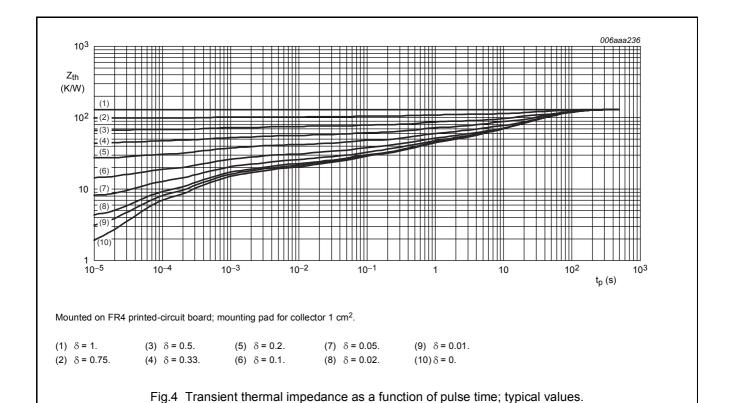
#### **Notes**

- 1. Device mounted on a printed-circuit board, single-sided copper, tin-plated and standard footprint.
- 2. Device mounted on a printed-circuit board, single-sided copper, tin-plated and mounting pad for collector 1 cm<sup>2</sup>.
- 3. Device mounted on a printed-circuit board, single-sided copper, tin-plated and mounting pad for collector 6 cm<sup>2</sup>.



# NPN high-voltage transistors

BF620; BF622



006aaa237 10<sup>3</sup>  $Z_{th}$ (K/W) 10<sup>2</sup> 10 . 10<sup>-5</sup> 10-4 10<sup>-3</sup> 10-2  $10^{-1}$ 10<sup>2</sup> 10 10<sup>3</sup> t<sub>p</sub> (s) Mounted on FR4 printed-circuit board; mounting pad for collector 6 cm<sup>2</sup>. (9)  $\delta = 0.01$ . (1)  $\delta = 1$ . (3)  $\delta = 0.5$ . (5)  $\delta = 0.2$ . (7)  $\delta = 0.05$ . (2)  $\delta = 0.75$ . (4)  $\delta = 0.33$ . (6)  $\delta = 0.1$ . (8)  $\delta = 0.02$ .  $(10) \delta = 0.$ Fig.5 Transient thermal impedance as a function of pulse time; typical values.

# NPN high-voltage transistors

BF620; BF622

### **CHARACTERISTICS**

 $T_{amb}$  = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I <sub>CBO</sub>	collector-base cut-off current	I <sub>E</sub> = 0 A; V <sub>CB</sub> = 200 V	_	10	nA
		I <sub>E</sub> = 0 A; V <sub>CB</sub> = 200 V; T <sub>j</sub> = 150 °C	_	10	μΑ
I <sub>EBO</sub>	emitter-base cut-off current	I <sub>C</sub> = 0 A; V <sub>EB</sub> = 5 V	_	50	nA
h <sub>FE</sub>	DC current gain	I <sub>C</sub> = 25 mA; V <sub>CE</sub> = 20 V	50	_	
V <sub>CEsat</sub>	collector-emitter saturation voltage	I <sub>C</sub> = 30 mA; I <sub>B</sub> = 5 mA	_	600	mV
C <sub>re</sub>	feedback capacitance	I <sub>C</sub> = i <sub>c</sub> = 0 A; V <sub>CE</sub> = 30 V; f = 1 MHz	_	1.6	pF
f <sub>T</sub>	transition frequency	$I_C = -10 \text{ mA}$ ; $V_{CE} = 10 \text{ V}$ ; $f = 100 \text{ MHz}$	60	_	MHz

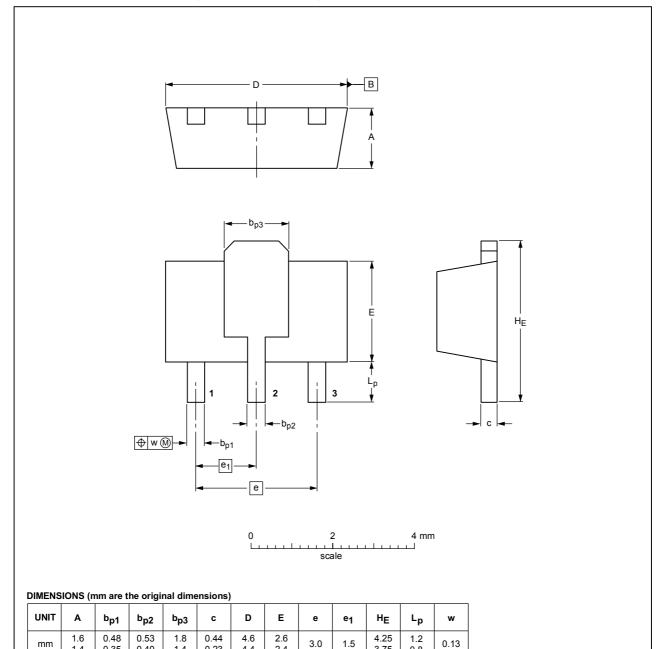
# NPN high-voltage transistors

BF620; BF622

### **PACKAGE OUTLINE**

### Plastic surface-mounted package; collector pad for good heat transfer; 3 leads

SOT89



OUTLINE REFERENCES		EUROPEAN	ISSUE DATE			
VERSION	IEC	JEDEC	JEITA		PROJECTION	1330E DATE
SOT89		TO-243	SC-62			<del>-04-08-03-</del> 06-03-16

3.75

2004 Dec 14 8

0.35

0.40

0.23

### NPN high-voltage transistors

BF620; BF622

#### **DATA SHEET STATUS**

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

#### **Notes**

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#### **Contact information**

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